



			DB - I	Time stamp
L	Hits	Search Text	מע	11mc Scamp
Number		susceptor and (sandblasting or blasted or	USPAT;	2003/03/10
1	16	blasting) and etch\$4 and (rinse or	EPO; JPO;	14:56
			IBM TDB	1
	2.5	rinsing) susceptor same (sandblasting or blasted	USPAT;	2003/03/10
2	25	or blasting)	EPO; JPO;	16:21
	ļ	or brasting,	IBM TDB	
	91	susceptor and (sandblasting or blasted or	USPAT;	2003/03/10
3	91	blasting)	EPO; JPO;	15:22
		prasting,	IBM_TDB	
	8	(susceptor or chuck or pedestal) same	USPAT;	2003/03/10
4		(glass or "silicon dioxide" or	EPO; JPO;	16:16
		"SiO.sub.2") same (sandblasting or	IBM_TDB	
		blasted or blasting)		/22/12
5	329	(susceptor or chuck or pedestal) and	USPAT;	2003/03/10
5	323	/~lage or "gilicon dioxide" or	EPO; JPO;	15:24
		"SiO.sub.2") and (sandblasting or blasted	IBM_TDB	
		or blasting)		0000 (00 (70
6	160	((susceptor or chuck or pedestal) and	USPAT;	2003/03/10
"	1 30	l/glass or "silicon dioxide" Or	EPO; JPO;	15:25
		"siO sub 2") and (sandblasting or blasted	IBM_TDB	
		or blasting)) and semiconductor		2003/03/10
7	18	l/susceptor or "substrate holder" or	USPAT;	2003/03/10
'		nedestal) and (glass or "silicon dloxide"	EPO; JPO;	16:20
		or "SiO sub.2") and (sandblasting or	IBM_TDB	
		blasted or blasting) and etch\$4 and	•	
		(rinse or rinsing)	HCDAT.	2003/03/10
8	133	(susceptor or jig) same (sandblasting or	USPAT; EPO; JPO;	16:28
		blasted or blasting)	IBM TDB	15.25
			USPAT;	2003/03/10
9	2030	(susceptor or jig) same etch\$4	EPO; JPO;	16:29
	Į.		IBM TDB	
		the same at about a same	USPAT;	2003/03/10
10	12		EPO; JPO;	16:31
		blast\$3	IBM TDB	
		de la company de	USPAT;	2003/03/10
11	32	(susceptor or jig) same etch\$4 same	EPO; JPO;	16:36
		(rinse or rinsing)	IBM TDB	†
		(SiC or "silicon carbide") same blast\$4	USPAT;	2003/03/10
12	752	(SIC OF SITICOII CAIDING / Same Brasey)	EPO; JPO;	16:37
			IBM TDB	
		((SiC or "silicon carbide") same blast\$4)	USPAT;	2003/03/10
13	51	and (susceptor or jig)	EPO; JPO;	16:37
		and (Susceptor or Jig/	IBM TDB	
L				